

Core-to-Core Program



Study on the readout of the ultra-low material RPC for background suppression in the MEG II experiment

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<u>Outline</u>

Introduction of RPC readout

- Pileup probability
- Prototype RPC readout
- Impedance matching
- Lab test
- Summary & prospects

<u>Pileup study</u>

Requirements for RPC

- 90% efficiency for 1-5 MeV e^+
- Rate capability $(10^8 \mu/s \text{ with } 21 \text{ MeV/c})$
- Pileup of high-rate μ^+ beam & RMD e^+
- → Inefficiency of RMD e^+
- → Readout strips should be segmented



<u>Pileup</u>

 Calculate pileup probability per readout segmented region









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- Characteristic impedance of AI strip: Z_S
- Characteristic impedance of LEMO cable: $Z_0 = 50 \ \Omega$
- Reflection coefficient $r = \frac{Z_0 Z_S}{Z_0 + Z_S}$
- $\rightarrow Z_0 = Z_S$ for no reflection (r = 0)
- Insert a resistor b/w AI strip & LEMO $\rightarrow Z_0' = R + Z_0$
- Then $r = \frac{Z_0' Z_S}{Z_0' + Z_S} \rightarrow$ Find R which gives r = 0 in lab test
- RPC threshold in our lab test is 10 mV

→ In lab test, find resistance which suppresses reflection to reduce deadtime

<u>Outline</u>

- Introduction of RPC readout
- Lab test
 - Setups
 - Waveform
 - Effect of resistors on RPC
- Summary & prospects



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Waveform

- Reflected height is dependent on signal height
- Reflection can be suppressed by inserting resistors
- Need to optimise resistance







<u>Outline</u>

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<u>Summary & prospects</u>

• Summary

- Readout w/o resistors generated reflection
- Resistors inserted b/w AI readout strip & LEMO cable can improve impedance matching
- Prospects
 - Compare w/ to w/o resistors in case of both readouts
 - Investigate reflected height quantitatively
 - Optimise readout and resistance

Backups

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<u>Physics of $\mu^+ \rightarrow e^+ \gamma$ </u>

- Charged lepton flavour violation (cLFV) is forbidden in the standard model (SM)
 - In the SM, $\mathcal{B}(\mu \to e \gamma) < 10^{-50}$
- Some physics models beyond the SM (SUSY-GUT, SUSY-seesaw) say $\mathcal{B}(\mu \rightarrow e\gamma)$ is $10^{-11} 10^{-14}$
- MEG experiment gave the upper limit of $\mu \rightarrow e\gamma 5.3 \times 10^{-13}$ for the branching ratio
- $\mu \rightarrow e\gamma$ observation strengthen makes models beyond SM



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<u>MEG II signal</u>

• MEG II searches for charged lepton flavour violating decay: $\mu^+ \rightarrow e^+ \gamma$



<u>MEG II background</u>

- Sources of e^+ , γ of around 52.8 MeV are these 3 reactions:
 - Michel decay
 - Radiative muon decay (RMD)
 - Annihilation in flight (AIF)



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Michel decay

RMD

Detect it!

BG properties

- RMD γ is identified from
 - RMD e^+ energy
 - Time correlation b/w e^+ & γ



Michel decay

RMD

 μ^+

 \mathbf{P}^{r}

e⁺

BG identification detectors

 Install radiative decay counters (RDCs) in both upstream and downstream



- High-intensity μ^+ beam passes through the upstream RDC
- ← Difficulty in developing it

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<u>Upstream RDC requirements</u>

1. Material budget: $< 0.1\% X_0$

($\leftarrow \mu^+$ beam passes through the detector)

- 2. 90% efficiency for e^+ with 1-5 MeV
- 3. 1 ns time resolution

(\leftarrow RMD ID with time difference b/w $e^+ \& \gamma$)

- 4. Rate capability & radiation hardness $(\leftarrow 7 \times 10^7 \mu^+/s \text{ with } 21 \text{ MeV/c } \& > 60 \text{ weeks run})$
- 5. Detector size: 20-cm diameter

(\leftarrow 45% acceptance in the one RDC, 90% in total w/ DS)

→ Ultra-low material resistive plate chamber (RPC)

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<u>RPC: Resistive Plate Chamber</u>

- RPC is one of gaseous detectors, uses high resistive electrodes placed face to face
- Gas is ionised when charged particles pass through RPC Ir
- Ionised electron is accelerated by high voltage (HV)
- Avalanche occurs by accelerated electrons
- Avalanche signals are induced in readout



<u>Pileup</u>

 Calculate pileup probability per readout region in which AI strips overlap







Pileup calculation

- *P_i*: pileup probability per readout segmented region
- ρ_i : probability to detect RMD e^+ in the segmented region (= 2.8 cm)
- Total pileup probability is given by
- $\sum_{strips=256} P_i \rho_i$
- Probability of time difference t b/w continuous μ^+ :
- $p(t) = \frac{1}{\tau} \exp\left(-\frac{t}{\tau}\right)$, where $\frac{1}{\tau}$ is μ^+ rate in region *i*
- Probability of pileup of μ^+ beam & RMD e^+ in region *i*:
- $P_i = 1 \exp\left(-\frac{t_{dead}}{\tau}\right)$, where t_{dead} is deadtime when we cannot distinguish μ^+ & RMD e^+

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Prototype RPC



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Transmission line

- Assume AI strip is a transmission line with loss
- Conductance G is zero

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C:単位長あたりのキャパシタンス

(単位長は扱う波長に対して、充分、小さい値で考える)

איטטא טודוווים ופטטטטרטרוווים טוונט-וטאי דוטופווטרגר כ-דטר טטכגעוטטווט

suppression in the MEG II experiment

<u>Resistance per length</u>

- Surface resistivity $R_S = 1.1 \Omega/sq$
- $\rightarrow R = \frac{R_S}{W} = 110 \,\Omega/\mathrm{m}$
- where W is width of AI strip, that is 1 cm

Property		Units	Aluminum Metallized Polyimide Film Typical Value	
			LR-PI 100AM	LR-PI 200AM
Backing Thickness		μm	25	50
Aluminum Thickness		μm	0.2-0.5	0.2-0.5
Tensile Strength		MPa	≥140	≥130
Elongation		%	≥45	≥45
Shrinkage, at 150°C		%	0.20	0.20
Surface Resistivity	The side of PI Film	Ω	≥1X10 ¹²	≥1X10 ¹²
	The side of Aluminum	Ω	<10 ³	<10 ³



Capacitance per length

- Think of geometry like this figure
- Ignore DLC plate because DLCs are sputtered on kaptons
- Kapton's relative permittivity $\varepsilon_r = 3.3$



Capacitance per length

- Give strip charge per length q
- From Gauss's raw, electric field is

•
$$q = \varepsilon_0 \varepsilon_r EW \to E = \frac{q}{\varepsilon_0 \varepsilon_r W}$$

• From the field, potential diff b/w Al strip and Cu pad is

•
$$V = \int_{0}^{d} \frac{q}{\varepsilon_{0}\varepsilon_{r}W} dx = \frac{qd}{\varepsilon_{0}\varepsilon_{r}W}$$

• From $V = \frac{q}{c'}$,
• $C_{i} = \frac{\varepsilon_{0}\varepsilon_{r}W}{d}$
Study on the readout of the ultra-low material RPC for background up ad 30
Study on the readout of the ultra-low material RPC for background up ad 30

Capacitance per length

- From $C_i = \frac{\varepsilon_0 \varepsilon_r W}{d}$, where C_i is capacitance per length in layer *i*
- Total capacitance $C = 155 \, \text{pF/m}$



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Inductance per length

- Think of geometry like this figure
- Assume current *I* flows only in Al strip (No current in Cu pad)
- From Ampere's raw, magnetic field is

•
$$2W\mu B = J \rightarrow B = \frac{\mu J}{2W}$$

• Permeability $\mu = \mu_0$



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Inductance per length

• Magnetic flux Φ is • $\Phi = \int \frac{\mu_0 J}{2W} dS = \frac{\mu_0 J}{2W} d$ • From Φ , calculate V, L • $V = -\frac{d\Phi}{dt} = -\frac{\mu_0 d}{2W} \frac{dJ}{dt} = -L\frac{dJ}{dt} \rightarrow L = \frac{\mu_0 d}{2W} \text{ H/m}$ • L = 44 nH/mtotal d = 695 umAl strip Kapton 1 d = 25 umKapton 2 d = 50 umKapton 3 d = 50 umDLC Gas d = 520 um Kapton 4 d = 50 umStudy on the readout of the ultra-low material RPC for background upda 33 16 Feb, 2020 suppression in the MEG II experiment

<u>Characteristic impedance</u>

- Need to consider resistance *R* because we cannot ignore loss
- Characteristic impedance is

•
$$|Z_0| = \sqrt{\frac{R^2 + (\omega L)^2}{(\omega C)^2}}$$

- where ω is angular frequency
- Assume signals are triangle waves whose width is 5 ns
- In this case, assume $\omega = 628 \text{ rad}/\mu \text{s}$

•
$$\rightarrow |Z_0| = \sqrt{\frac{R^2 + (\omega L)^2}{(\omega C)^2}} = 17 \Omega$$

• But I estimate $Z_0 > 50 \Omega$ from observation of reflection

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RPC performance w/ resistors

Height

histHeight

32326

0.004952

0.009708

Entries

Std Dev

R = 150 ohm

Mean

histHeight2

32326

0.004063

0.007968

Entries

Std Dev

Mean

Each histogram expresses voltage height induced in each side
Height is dependent on resistance because voltage

drop occurs at resistors



RPC performance w/ resistors

- These histograms express the sum of voltage at both sides of Al strip
- Height sum is dependent on ٠ resistance because voltage drop occurs at resistors as well as height from each side



Height

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0.1

Count [a.u]

10³

10²

10

1